

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7W00F, TC7W00FU, TC7W00FK

DUAL 2-INPUT NAND GATE

The TC7W00 is a high speed C²MOS 2-INPUT NAND GATE fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the C²MOS low power dissipation.

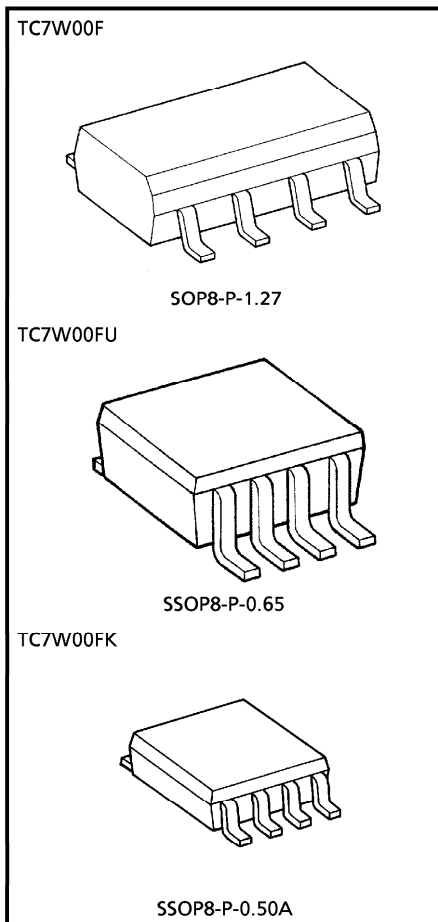
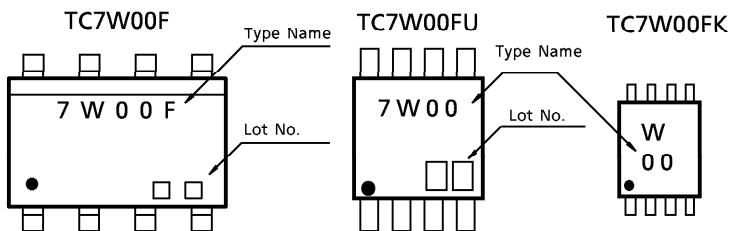
The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

- High Speed $t_{pd} = 6\text{ns}$ (Typ.) at $V_{CC} = 5\text{V}$
- Low Power Dissipation $I_{CC} = 1\mu\text{A}$ (Max.) at $T_a = 25^\circ\text{C}$
- High Noise Immunity $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Output Drive Capability 10 LSTTL Loads
- Symmetrical Output Impedance ... $|I_{OH}| = I_{OL} = 4\text{mA}$ (Min.)
- Balanced Propagation Delays $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range ... $V_{CC}(\text{opr}) = 2\sim 6\text{V}$

MARKING



Weight	
SOP8-P-1.27	: 0.05g (Typ.)
SSOP8-P-0.65	: 0.02g (Typ.)
SSOP8-P-0.50A	: 0.01g (Typ.)

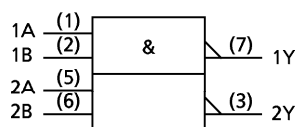
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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V _{CC}	-0.5~7	V
DC Input Voltage	V _{IN}	-0.5~V _{CC} +0.5	V
DC Output Voltage	V _{OUT}	-0.5~V _{CC} +0.5	V
Input Diode Current	I _{IK}	±20	mA
Output Diode Current	I _{OK}	±20	mA
DC Output Current	I _{OUT}	±25	mA
DC V _{CC} /Ground Current	I _{CC}	±25	mA
Power Dissipation	P _D	300 (FM8, SM8)	mW
		200 (US8)	
Storage Temperature	T _{stg}	-65~150	°C
Lead Temperature (10s)	T _L	260	°C

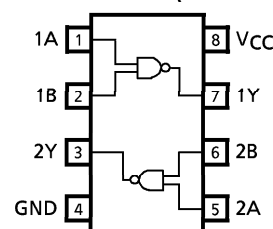
LOGIC DIAGRAM



TRUTH TABLE

A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

PIN ASSIGNMENT (TOP VIEW)



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	2~6	V
Input Voltage	V _{IN}	0~V _{CC}	V
Output Voltage	V _{OUT}	0~V _{CC}	V
Operating Temperature	T _{opr}	-40~85	°C
Input Rise and Fall Time	t _r , t _f	0~1000 (V _{CC} = 2.0V)	ns
		0~500 (V _{CC} = 4.5V)	
		0~400 (V _{CC} = 6.0V)	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{CC}	Ta = 25°C			Ta = -40~85°C		UNIT									
				MIN.	TYP.	MAX.	MIN.	MAX.										
High-Level Input Voltage	V _{IH}	—	2.0	1.5	—	—	1.5	—	V									
			4.5	3.15	—	—	3.15	—										
			6.0	4.2	—	—	4.2	—										
Low-Level Input Voltage	V _{IL}	—	2.0	—	—	0.5	—	0.5	V									
			4.5	—	—	1.35	—	1.35										
			6.0	—	—	1.8	—	1.8										
High-Level Output Voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -20μA	2.0	1.9	2.0	—	1.9	—	V								
				4.5	4.4	4.5	—	4.4	—									
				6.0	5.9	6.0	—	5.9	—									
Low-Level Output Voltage	V _{OL}	V _{IN} = V _{IH}	I _{OL} = 20μA	2.0	—	0.0	0.1	—	0.1	V								
				4.5	—	0.0	0.1	—	0.1									
				6.0	—	0.0	0.1	—	0.1									
Input Leakage Current	I _{IN}	V _{IN} = V _{CC} or GND	6.0	—	—	±0.1	—	±1.0	μA									
										Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND	6.0	—	—	1.0	—	10.0

AC ELECTRICAL CHARACTERISTICS (C_L = 15pF, V_{CC} = 5V, Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta = 25°C			UNIT
			MIN.	TYP.	MAX.	
Output Transition Time	t _{TLH}	—	—	4	8	ns
	t _{THL}					
Propagation Delay Time	t _{pLH}	—	—	6	12	ns
	t _{pHL}					

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	V_{CC}	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t_{TLH}	—	2.0	—	25	75	—	95	ns
	t_{THL}		4.5	—	7	15	—	19	
			6.0	—	6	13	—	16	
Propagation Delay Time	t_{pLH}	—	2.0	—	27	75	—	95	ns
	t_{pHL}		4.5	—	9	15	—	19	
			6.0	—	8	13	—	16	
Input Capacitance	C_{IN}	—	—	5	10	—	10	pF	
Power Dissipation Capacitance	C_{PD}	(Note 1)	—	20	—	—	—		

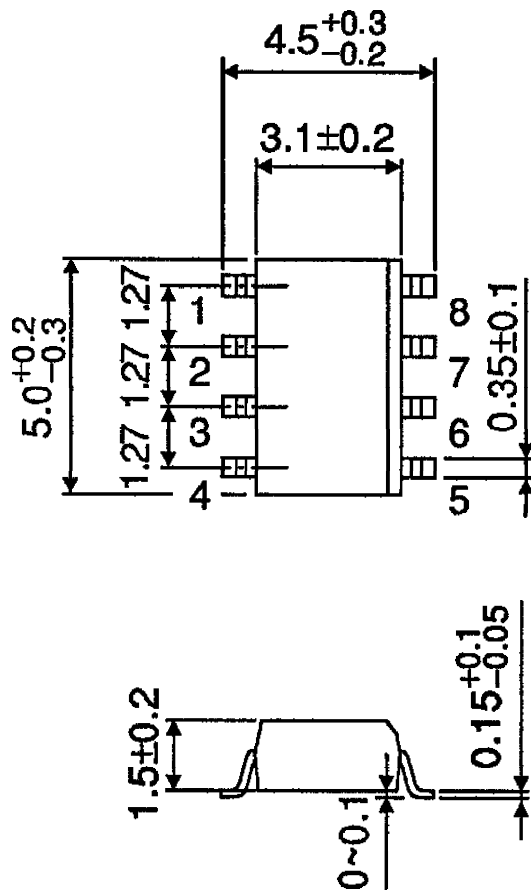
(Note 1) C_{PD} is defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

Average operating current can be obtained by the equation hereunder.

$$I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 2 \text{ (per gate)}$$

OUTLINE DRAWING
SOP8-P-1.27

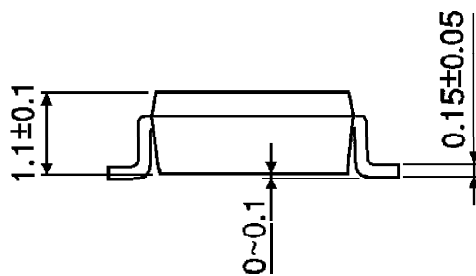
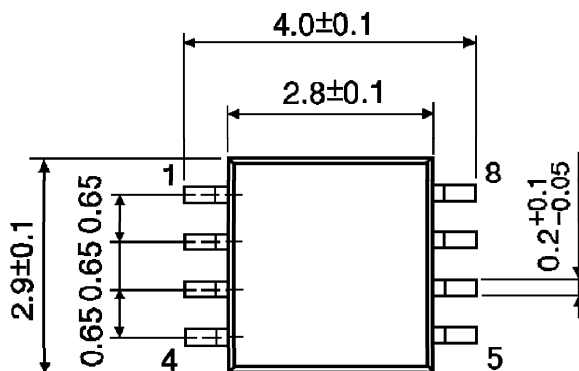
Unit : mm



Weight : 0.05g (Typ.)

OUTLINE DRAWING
SSOP8-P-0.65

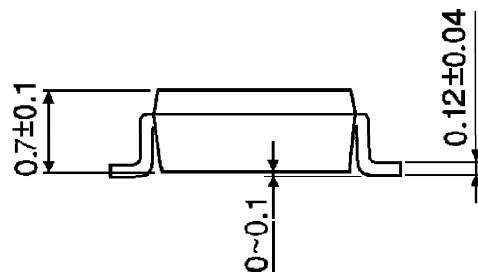
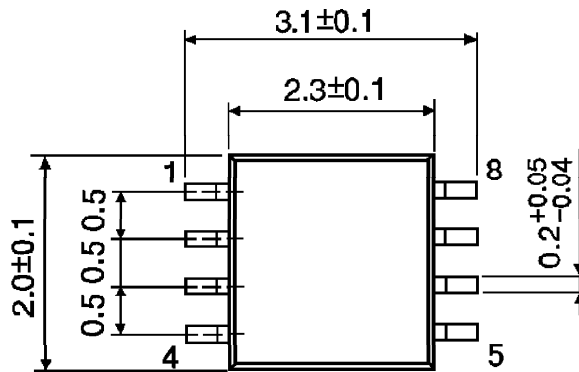
Unit : mm



Weight : 0.02g (Typ.)

OUTLINE DRAWING
SSOP8-P-0.50A

Unit : mm



Weight : 0.01g (Typ.)